

Form PTO-1449

US DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICE

**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**

(use as many sheets as necessary)

Complete if Known

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| Application Number | 10/690,290 |
| Filing Date | October 21, 2003 |
| First Named Inventor | Yuji HORI |
| Art Unit | 2814 |
| Examiner Name | Ngan V. Ngo |
| Confirmation No. | 4572 |
| Attorney Docket No. | 782_202 DIV2 |

Sheet 1 of 1

U.S. PATENT DOCUMENTS

| Exam. Initial | | Document Number | Date | Name | Our Docket No. | Class | Sub Class | Filing Date |
|---------------|-----|-----------------|------------|-----------------|----------------|-------|-----------|-------------|
| UH | AA* | 5,990,495 | 11-23-1999 | Ohba, Yasuo | | | | |
| UH | AB* | 6,064,082 | 05-16-2000 | Kawai et al. | | | | |
| UH | AC* | 5,810,925 | 09-22-1998 | Tadatomo et al. | | | | |
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U.S. COPENDING APPLICATIONS

| Exam. Initial | | Application/ Publication Number | Filing/ Publication Date | Inventor Name | Our Docket No. | Class | Sub Class |
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FOREIGN PATENT DOCUMENTS

| | | Document Number | Date | Country | Class | Sub Class | Translation | Abstract |
|----|----|-----------------|------------|---------|-------|-----------|-------------|----------|
| UH | AD | WO 98/35388 | 08-13-1998 | US | | | | |
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OTHER DOCUMENTS

(Including Author, Title, Date, Pertinent Pages etc.)

| | | |
|----|----|-----------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------------|
| UH | AE | M.A. Khan et al., "High Electron Mobility Transistor Based on a GaN-Al _x Ga _{1-x} N Heterojunction," Applied Physics Letters, 30 August 1993, USA, Vol. 63, No. 9, pages 1214-1215, XP002269124 |
| UH | AF | P. Kung et al., "High Quality AlN and GaN Epilayers Grown on (pp.1) Sapphire, (100) and (111) Silicon Substrates," Applied Physics Letters, American Institute of Physics, NY, US, Vol. 66, No. 22, 29 May 1995, pages 2958-2960, XP000507525 |

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|-----------|--------------------|------------------|----------|
| Examiner: | <i>Ngan V. Ngo</i> | Date Considered: | 06/04/04 |
|-----------|--------------------|------------------|----------|

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

*In accordance with the Notice dated July 11, 2003 on the PTO website, we are not enclosing copies of any of the U.S. references listed above.